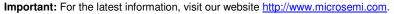




Switching Diode Array Steering Diode TVS Array[™]

DESCRIPTION

These low capacitance diode arrays are multiple, discrete, isolated junctions fabricated by a planar process and mounted in a 14-Pin DIP package for use as steering diodes protecting up to eight I/O ports from ESD, EFT, or surge by directing them either to the positive side of the power supply line or to ground (see figure 1). An external TVS diode may be added between the positive supply line and ground to prevent overvoltage on the supply rail. They may also be used in fast switching core-driver applications. This includes computers and peripheral equipment such as magnetic cores, thin-film memories, plated-wire memories, etc., as well as decoding or encoding applications. These arrays offer many advantages of integrated circuits such as high-density packaging and improved reliability. This is a result of fewer pick and place operations, smaller footprint, smaller weight, and elimination of various discrete packages that may not be as user friendly in PC board mounting. They are available with either Tin-Lead plating terminations or as RoHS Compliant with annealed matte-Tin finish.



FEATURES

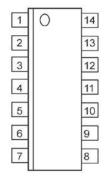
- 14 diode array protects 8 lines
- Molded 14-Pin dual-in-line package
- UL 94V-0 flammability classification
- Low capacitance
- Switching speeds less than 5 ns
- Discrete diode elements offer optimum isolation
- IEC 61000-4 compatible:

61000-4-2 (ESD): Air 15 kV, contact – 8 kV

61000-4-4 (EFT): 40 A – 5/50 ns 61000-4-5 (surge): 12 A, 8/20 μs

RoHS compliant device is available

14 Pin Package



Top Viewing Pin Layout

APPLICATIONS / BENEFITS

- Low capacitance steering diode protection for high frequency data lines
- Ideal for:

RS-232 & RS-422 Interface Networks.

Ethernet: 10 Base T Computer I/O Ports

LAN

Switching Core Drivers

MSC - Lawrence

6 Lake Street, Lawrence, MA 01841 Tel: 1-800-446-1158 or (978) 620-2600 Fax: (978) 689-0803

MSC - Ireland

Gort Road Business Park, Ennis, Co. Clare, Ireland Tel: +353 (0) 65 6840044 Fax: +353 (0) 65 6822298

Website:

www.microsemi.com



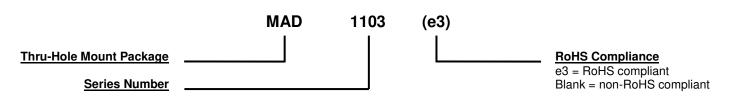
MAXIMUM RATINGS

Parameters/Test Conditions	Symbol	Value	Unit
Junction and Storage Temperature	T_J and T_{STG}	-55 to +150	ºC/W
Peak Working Reverse Voltage	V_{RWM}	75	V
Repetitive Peak Forward Current (one diode)	I _{FRM}	400	mA
Forward Surge Current @ 8.3 m	s I _{FSM}	2	Α
@ 8/20 _l	s	12	
Rated Average Power dissipation (total)	P _{M(AV)}	1500	mW
Solder Temperature @ 10 s		260	ºC

MECHANICAL and PACKAGING

- CASE: Void-free transfer molded thermosetting epoxy body meeting UL94V-0 flammability classification
- TERMINALS: Tin-lead or RoHS compliant annealed matte-tin plating solderable per MIL-STD-750 method 2026
- MARKING: MSC logo, MAD1103 or MAD1103e3 and date code. Pin #1 is to the left of the dot or indent on top of package.
- DELIVERY OPTION: Carrier tube. Consult factory for quantities
- WEIGHT: Approximately 0.997 grams
- See Package Dimensions on last page.

PART NOMENCLATURE



SYMBOLS & DEFINITIONS				
Symbol	Definition			
C _T	Total Capacitance: The total small signal capacitance between the diode terminals of a complete device.			
I_{R}	Reverse Current: The dc current flowing from the external circuit into the cathode terminal at the specified voltage V _R .			
V _(BR)	Breakdown Voltage: The voltage across the device at a specified current I _(BR) in the breakdown region.			
V_{F}	Forward Voltage: A positive dc anode-cathode voltage the device will exhibit at a specified forward current.			
V _{RWM}	Working Peak Reverse Voltage: The peak voltage excluding all transient voltages (ref JESD282-B). Also sometimes known historically as PIV.			

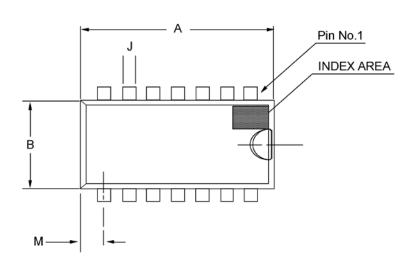
ELECTRICAL CHARACTERISTICS @ 25 °C unless otherwise stated

PART NUMBER	BREAKDOWN VOLTAGE V _(BR) @ I _(BR) =100 μA	LEAK CURF II T _A = 2	RENT	LEAKAGE CURRENT I _R T _A = 150 °C		CAPACITANCE C _T @ 0 V	REVERSE RECOVERY TIME t _{rr}	FORWARD VOLTAGE V _F I _F = 10 mA	FORWARD VOLTAGE V _F I _F = 100 mA
	V	μ	A	μ	Α	pF	ns	V	V
	MIN	MAX	@ V _R	MAX	@V _R	TYP (Note 1)	MAX	MAX	MAX
MAD1103 MAD1103e3	90	0.200	20	300	20	1.5	5.0	1.00	1.20

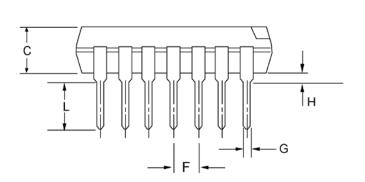
NOTE 1: Individual diode capacitance is less than 1.5 pF but will read higher between pins with the connected parallel diode array shown.

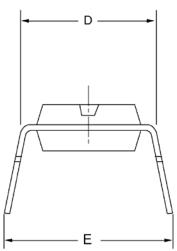


PACKAGE DIMENSIONS

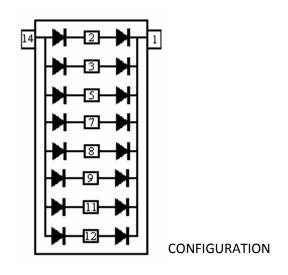


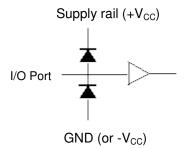
	Dimensions							
Ref.	Ir	nch	Millimeters					
	Min	Max	Min	Max				
Α	0.746	0.754	18.95	19.15				
В	0.246	0.254	6.248	6.452				
С	0.126	0.134	3.200	3.404				
D	0.300	0.325	7.619	8.255				
Е	0.320	0.370	8.128	9.398				
F	0.098	0.102	2.489	2.591				
G	0.016	0.020	0.406	0.508				
Н	0.015	0.040	0.381	1.016				
7	0.058	0.062	1.473	1.575				
L	0.121	0.129	3.073	3.277				
М	0.25	REF	0.635 REF					





CIRCUIT





STEERING DIODE APPLICATION